

Appl. No. 10/620,492
Reply to Office action of 12/01/2004

Amendments to the Specification:

Amend the second paragraph on page 7 as follows:

To form the device 100, a layer of dielectric material 424 108 such as silicon dioxide is initially formed over the substrate 102 (Fig. 2). A gate electrode layer 426 106 (e.g., polysilicon) is then formed over the layer of dielectric material 424 108 (Fig. 3). The gate electrode layer 426 106 and the layer of dielectric material 424 108 are then patterned (e.g., *via* etching) to develop the gate structure 104 (Fig. 4). Dopant 128 is then applied to the gate electrode 106 (e.g., *via* implantation) and to exposed portions of the substrate 102 to form extension regions 130, 132 therein (Fig. 5). As will become apparent, the extension regions 130, 132 are precursors to portions of the source and drain regions 118, 120 formed within the substrate 102.